

Abstract**Method And Device For Producing A Single Crystal Of Silicon, Which Single Crystal Is Doped With n-type Dopant**

The invention relates to a method and to a device for producing a single crystal of silicon, which single crystal is doped with n-type dopant and has, in a cylindrical portion, an electrical resistivity of not more than 2 mohm cm, by pulling the single crystal in accordance with the CZ method from a melt, which is contained in a crucible. The method comprises feeding a gas stream containing gaseous dopant to a surface of the melt in the course of the pulling of the cylindrical portion of the single crystal and is characterized in that the gas stream is conducted in a pipeline system into a pulling chamber and through a heat shield, which surrounds the growing single crystal, or along an outer surface of the heat shield, to a ring channel at a lower end of the heat shield and from there through nozzles to the surface of the melt.

Fig. 1